



IPHONE

4



www.GSM

# IPHONE 4

ژوئن ۲۰۱۰  
 GSM 850 / 900 / 1800 / 1900  
 ۱۵۰.۲ \* ۵۸.۶ \* ۹.۳ میلیمتر  
 ۱۳۷ گرم  
 ساده  
 مشکی/سفید  
 TFT touchscreen با صفحه لمسی خازنی  
 ۱۶ میلیون رنگ  
 ۶۴۰ \* ۹۶۰ پیکسل  
 ۳.۵ اینچ  
 MP3  
 بله  
 بله  
 تقریباً نامحدود برای شماره و مشخصه به همراه تصویر تماس گیرنده  
 -اتماس گرفته شده، تماس دریافت شده، تماس از دست رفته  
 ۱۶ کیگابایت یا ۳۲ کیگابایت  
 خیر  
 خیر  
 بله نسخه ۲.۱ با قابلیت ارسال همزمان داده ها BLUETOOTH STEREO  
 خیر  
 بله، نسخه ۲  
 بله  
 SMS (threaded view), MMS, Email, Push Email  
 HTML (Safari)  
 Wi-Fi 802.11 b/g/n  
 خیر  
 Class 10 (4+1/3+2 slots), 32 - 48 kbps  
 Class 10, 236.8 kbps  
 HSDPA 7.2 Mbps, HSUPA 5.76 Mbps  
 خیر  
 بله  
 بله/A-GPS support  
 ۵ مگاپیکسل  
 ۲۵۹۲ \* ۱۹۴۴ پیکسل  
 بله  
 LED flash/ LED video light  
 بله  
 به میزان حافظه  
 ۷۲۰ پیکسل، حداکثر ۳۰ فریم در ثانیه  
 بله  
 بله  
 بله  
 iOS 4 (based on Mac OS)  
 Apple A4 processor  
 (virtual QWERTY) بله  
 بله  
 بله

مشخصات کلی  
 معرفی  
 باند فرکانس  
 ابعاد  
 وزن  
 شکل ظاهری  
 رنگ  
 نوع  
 تعداد رنگ  
 وضوح  
 ابعاد  
 نوع رنگ  
 دریافت رنگ  
 لرزاننده  
 دفترچه تلفن  
 گزارش تماس ها  
 حافظه داخلی  
 پشتیبانی کارت حافظه  
 کارت حافظه همراه  
 بلوتوث  
 مادون قرمز  
 USB  
 انطباق با کامپیوتر  
 پیام  
 مرورگر اینترنت  
 شبکه بیسیم  
 چاپ مستقیم  
 GPRS  
 EDGE  
 G۳  
 PUSH TO TALK  
 PNP  
 GPS  
 کیفیت عکس  
 ابعاد عکس  
 بزرگنمایی  
 فلاش  
 فیلمبرداری  
 مدت فیلمبرداری  
 ابعاد فیلم  
 فوکوس خودکار  
 دوربین دوم  
 تماس تصویری  
 سیستم عامل  
 CPU  
 صفحه کلید کامل (QWERTY)  
 پخش فیلم  
 پخش موسیقی

راديو  
 کار با پرونده های آفیس  
 کار با پرونده های پی دی اف  
 کار با پرونده های زیپ  
 پخش با صدای بلند  
 پایه خروجی صدا  
 ساعت  
 رنگ هشدار  
 جاوا  
 بازی  
 نصب بازی  
 پیش بینی کلمه  
 شماره گیری صوتی  
 ضبط صدا  
 خروجی تلویزیون  
 مدیریت اطلاعات شخصی  
 ویرایش فیلم  
 سنسور حرکتی  
 مشخصات ویژه این مدل  
 نوع  
 مکالمه  
 انتظار  
 خیر  
 بله  
 بله  
 بله  
 بله  
 mm audio jack ۳.۵  
 بله  
 بله  
 بله  
 خیر  
 بله با ساپورت بازی های حرکتی  
 بله  
 بله  
 T9  
 بله  
 بله  
 بله  
 تقویم / دفترچه تلفن / یادداشت/وظایف آتی/ماشین حساب و ...  
 بله  
 دسگر شتاب سنج برای چرخش اتوماتیک صفحه نمایش / Proximity sensor for auto turn-off  
 صفحه نمایش ضد خش/نویزگیر صدا با میکروفن مجزا/پنل پشت گوشی از جنس شیشه  
 ضدخش/فوکوس لمسی/  
 geo-tagging/Multi-touch input method/Three-axis sensor/Google Maps/iBooks application gyro  
 باتری استاندارد Li-Ion  
 حداکثر ۴ ساعت  
 حداکثر ۳۰۰ ساعت

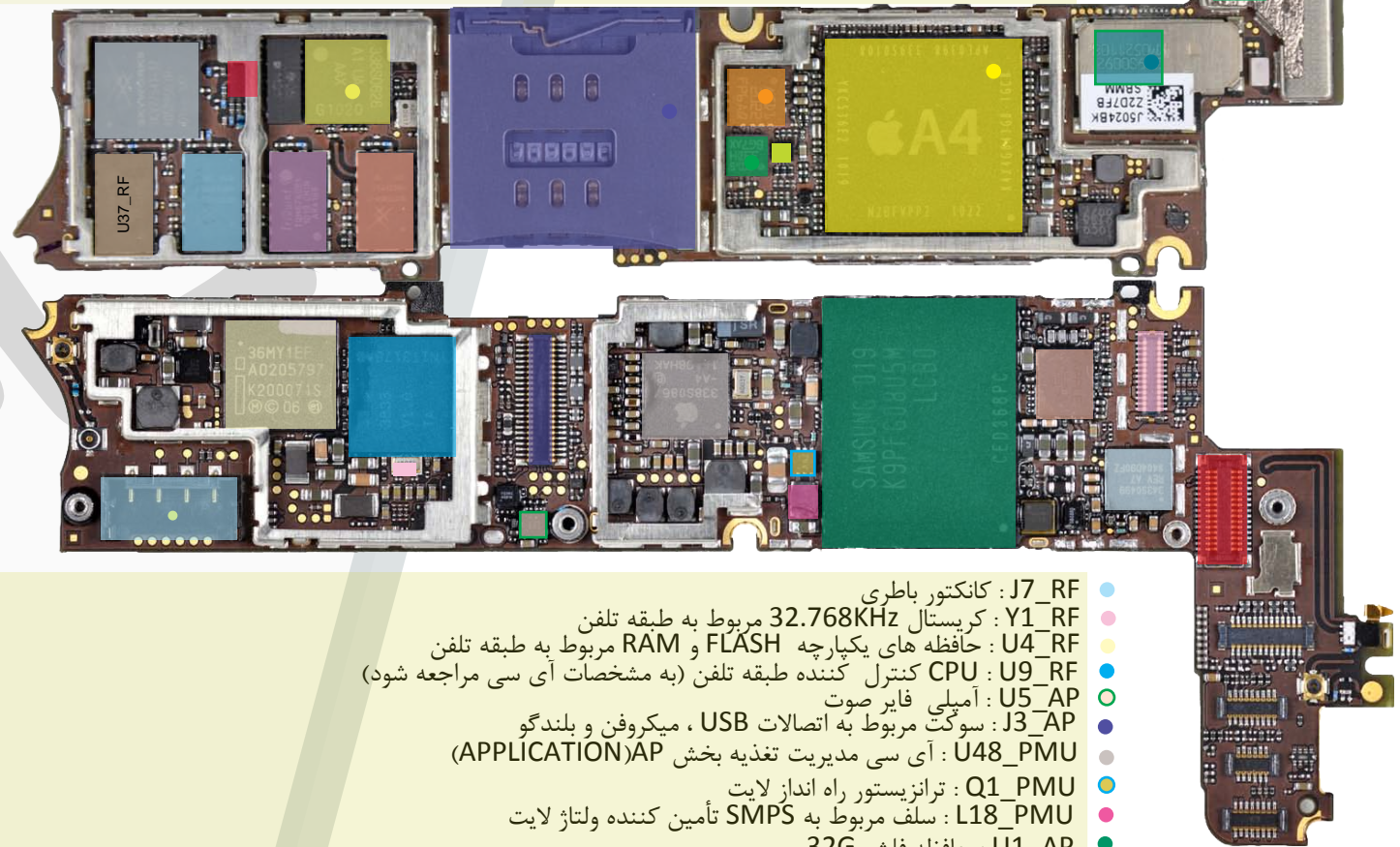


IPHONE

4



- U1\_RF : آمپلی فایر مربوط به طبقه فرستنده بخش GSM
- U37\_RF : تقویت کننده رادیویی (باند ۲) مربوط به بخش WCDMA و HSUPA
- U5\_RF : تقویت کننده رادیویی (باند ۶و۵) مربوط به بخش WCDMA و HSUPA
- U19\_RF : تقویت کننده رادیویی (باند ۱) مربوط به بخش WCDMA و HSUPA
- U20\_RF : تقویت کننده رادیویی (باند ۸) مربوط به بخش WCDMA و HSUPA
- U8\_RF : آی سی RFSP (پردازشگر طبقه رادیویی) ساخت کمپانی INFINEON که مدیریت طبقه رادیویی را برعهده دارد
- U6\_RF : تقویت کننده LNA مربوط به بخش RX طبقات WCDMA و HSUPA
- J2\_AP : سوکت سیم کارت
- U3\_AP : سنسور شتاب به منظور تشخیص جابجایی گوشی
- U16\_AP : GYRO یا ژيروسکوپ برای تشخیص جابجایی گوشی
- U9\_AP : تقویت کننده تصویر مربوط به اتصال کابل AV
- U52\_AP : پردازشگر و کنترل کننده طبقه APPLICATION
- U2\_RF : ماژول WLAN ، بلوتوس و رادیو FM
- U14\_RF : ماژول GPS

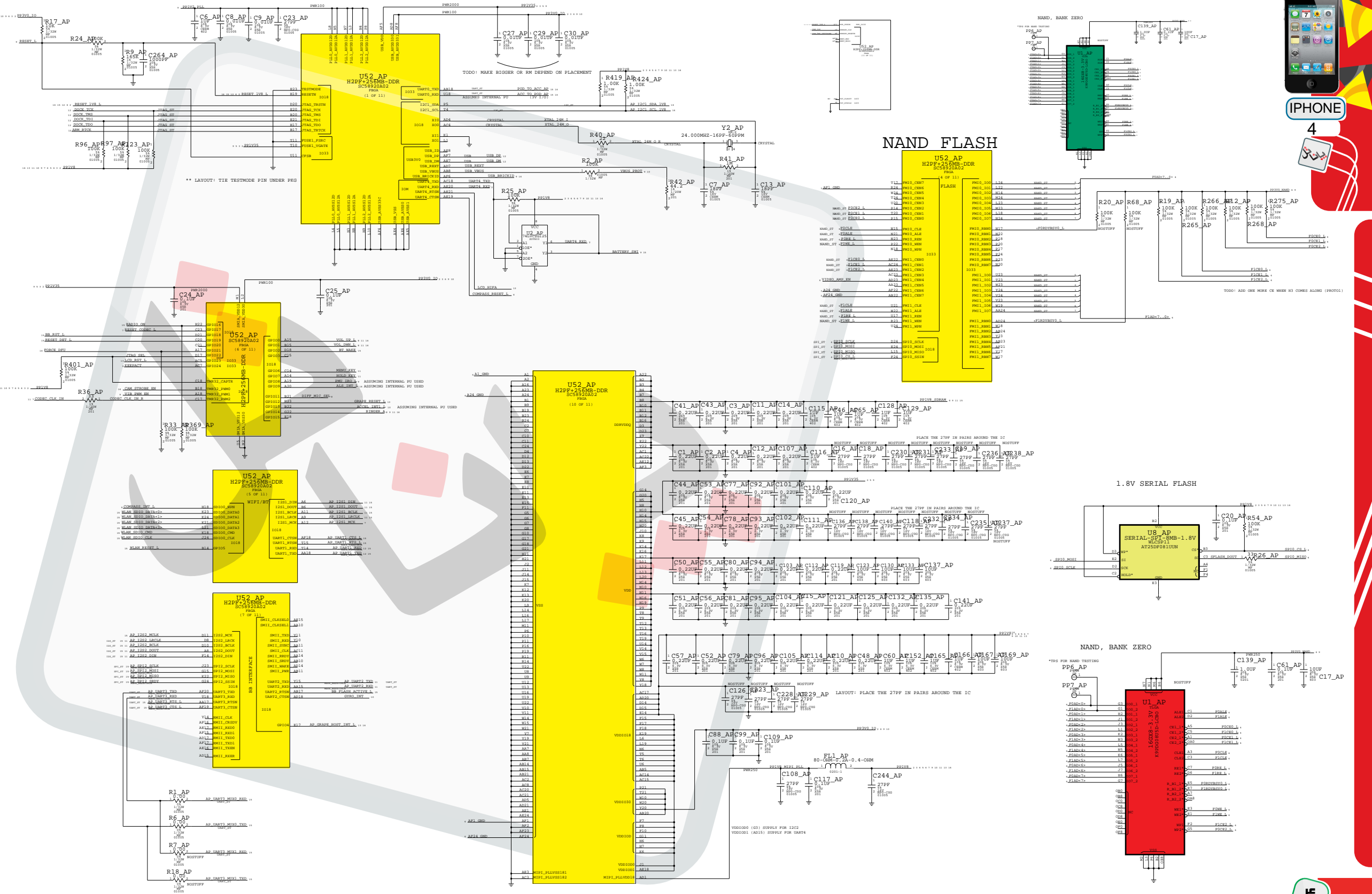


● برای بدست آوردن اطلاعات بیشتر توصیه می شود به اطلاعات فنی آی سی ها در انتها مراجعه شود ●

- J7\_RF : کانکتور باتری
- Y1\_RF : کریستال 32.768KHZ مربوط به طبقه تلفن
- U4\_RF : حافظه های یکپارچه FLASH و RAM مربوط به طبقه تلفن
- U9\_RF : CPU کنترل کننده طبقه تلفن (به مشخصات آی سی مراجعه شود)
- U5\_AP : آمپلی فایر صوت
- J3\_AP : سوکت مربوط به اتصالات USB ، میکروفن و بلندگو
- U48\_PMU : آی سی مدیریت تغذیه بخش AP (APPLICATION)
- Q1\_PMU : ترانزیستور راه انداز لایت
- L18\_PMU : سلف مربوط به SMPS تأمین کننده ولتاژ لایت
- U1\_AP : حافظه فلش 32G
- U60\_AP : آی سی کنترل و مدیریت صوت
- U19\_AP : آی سی کنترل کننده صفحه لمسی
- J5\_AP : کانکتور صفحه لمسی
- J6\_AP : کانکتور دوربین



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TODD: MAKE BIGGER OR SM SMALLER DEPENDING ON PLACEMENT

NAND FLASH

1.8V SERIAL FLASH

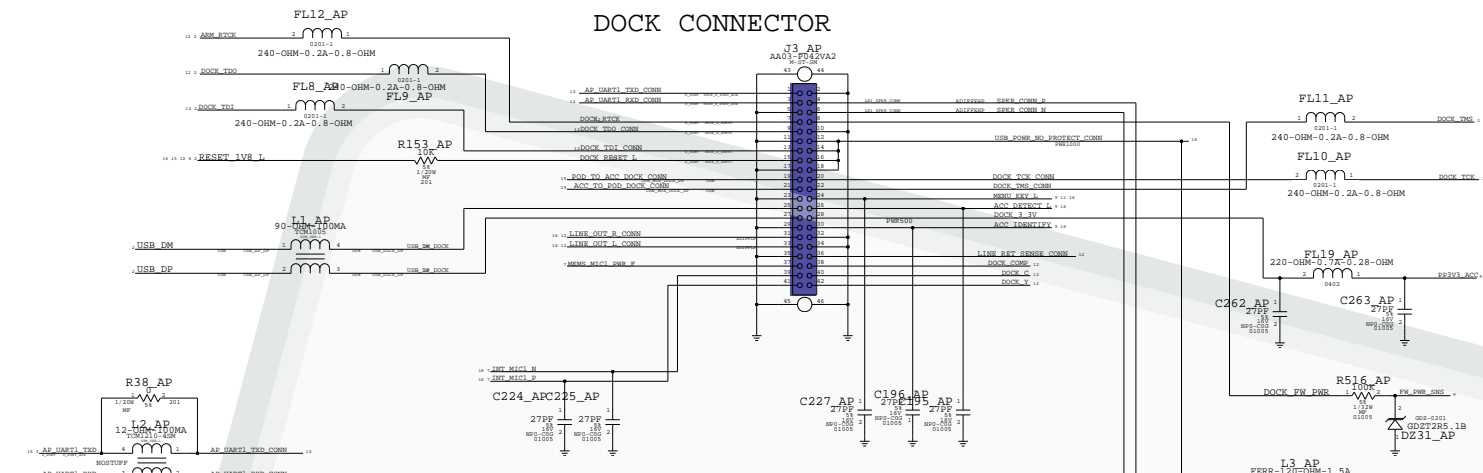
NAND, BANK ZERO





IPHONE 4

### DOCK CONNECTOR

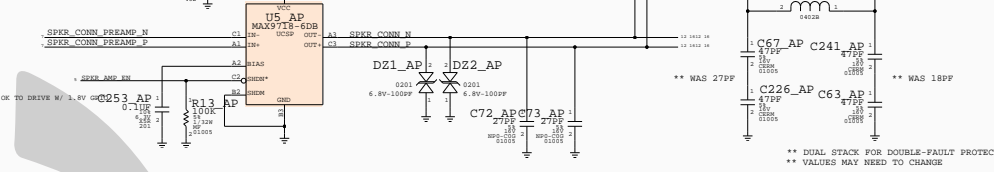


\* DISPLAYPORT, DUAL FOOT PLACOLDERS

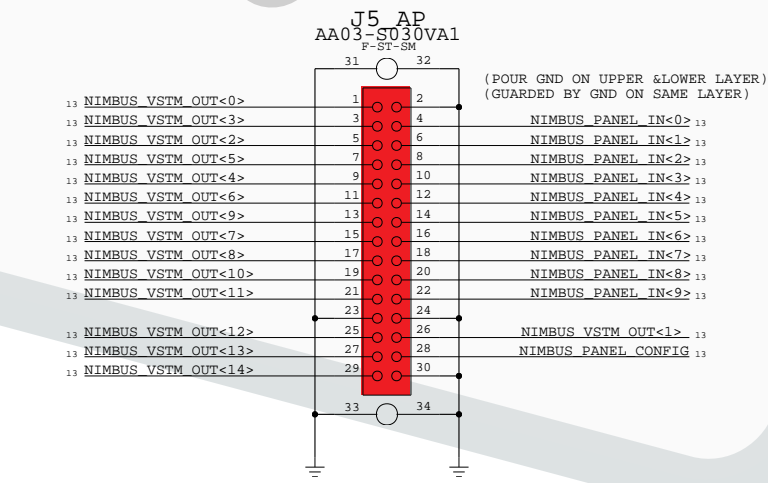
\* LAYOUT: NEST R153 AND FL8 W/ L6

\* LAYOUT: NEST FL9 AND FL12 W/ L5

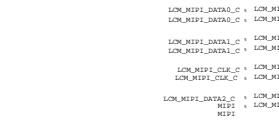
### SPKR PREAMP



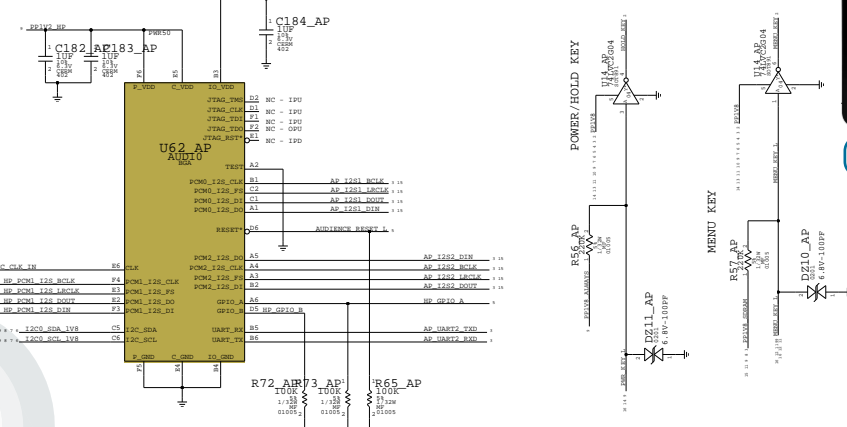
### GRAPE CONNECTOR N90 NIMBUS CONNECTOR



### N90 LCD CONNECTOR



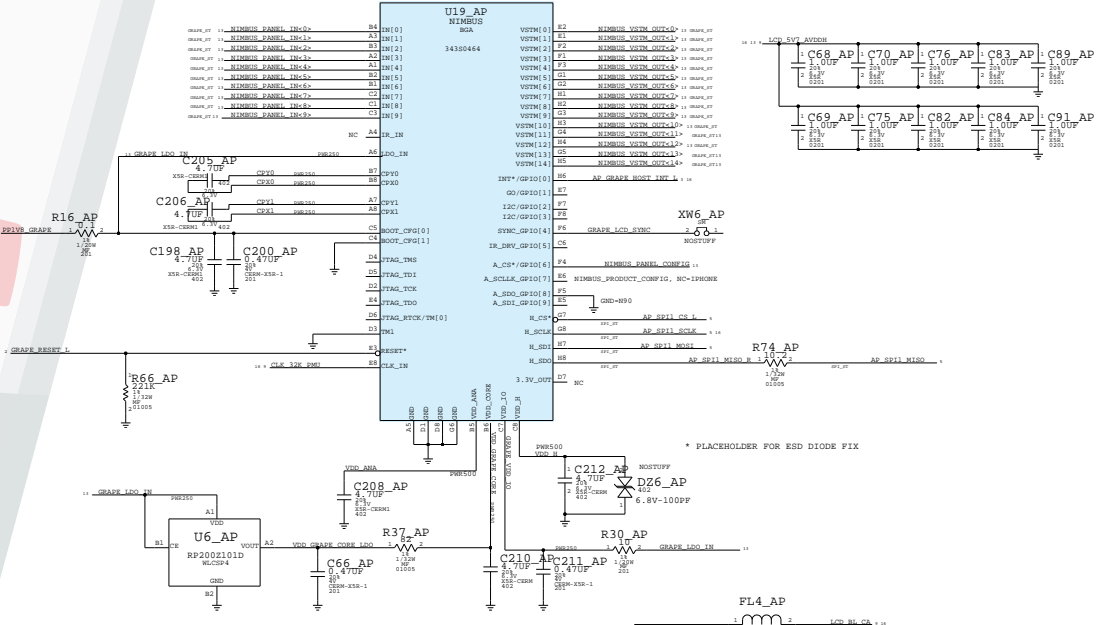
I2C ADDRESS: 0111110X (0X3E)



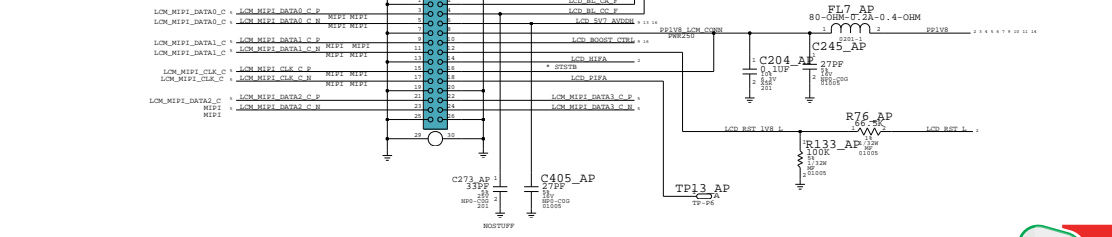
### VOLUME SWITCHES

### RINGER A/B SWITCH R58 AP

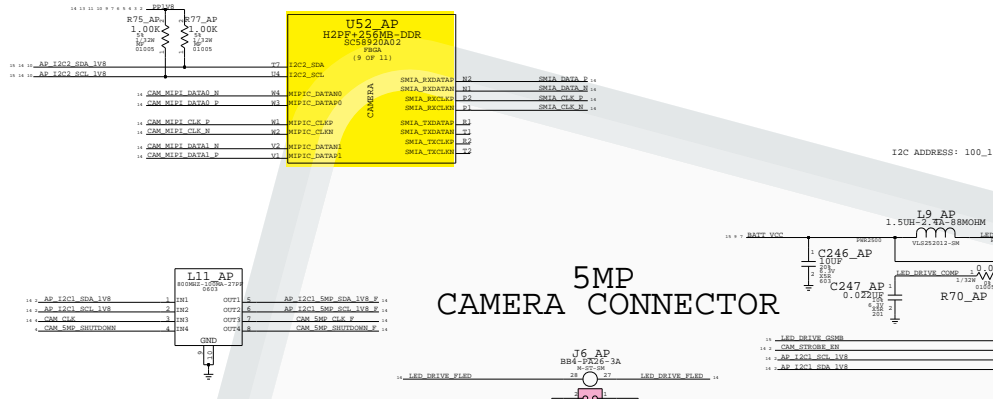
### NIMBUS



### N90 LCD CONNECTOR



# CAMERA INTERFACE

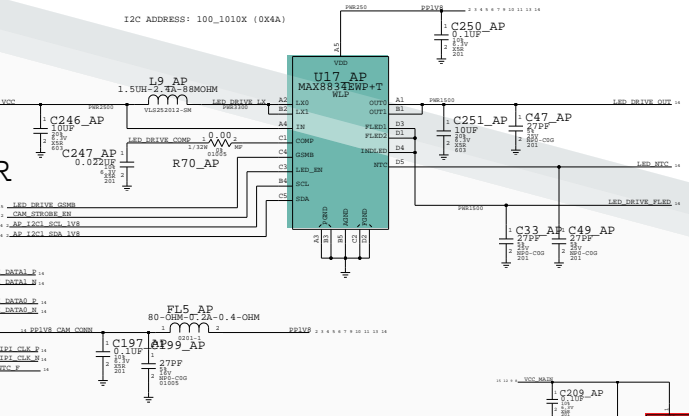


## 5MP CAMERA CONNECTOR

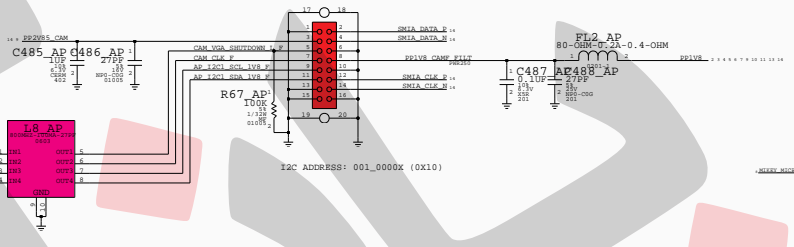
## ALS/PROX

## LED DRIVER

\* PLACE CLOSE TO BATTERY \*



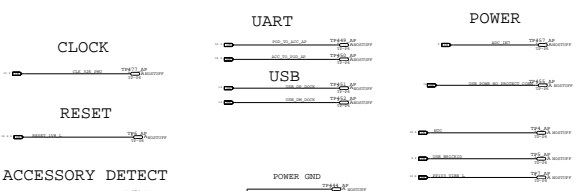
## VGA CAMERA CONN



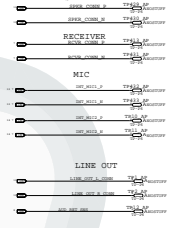
## GPIO



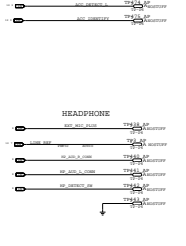
## TEST POINTS



## AUDIO



## ACCESSORY DETECT



## UART



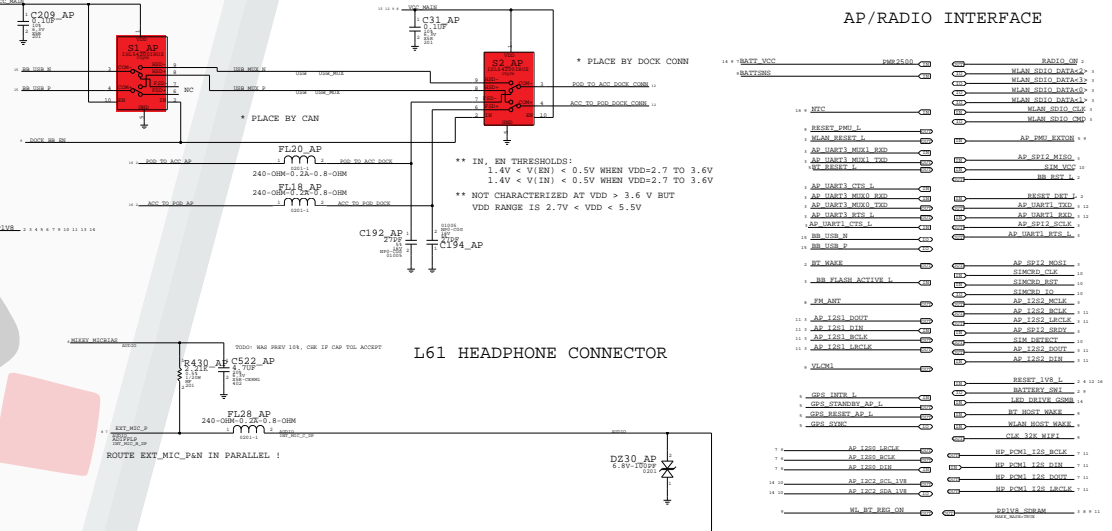
## POWER



IPHONE

4

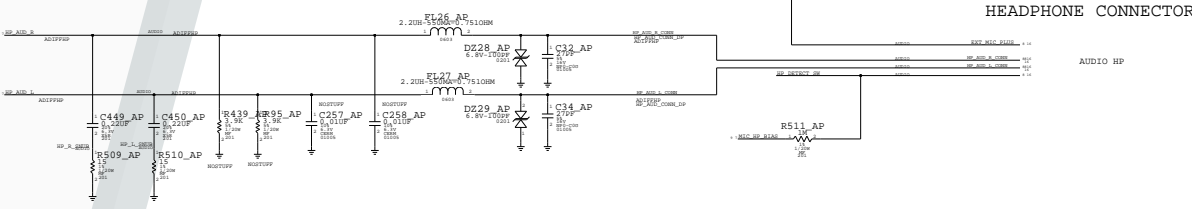
## AP/RADIO INTERFACE



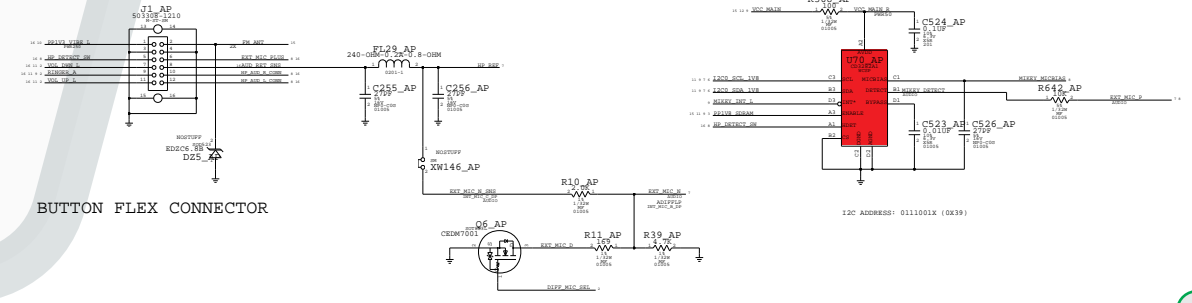
## L61 HEADPHONE CONNECTOR



## HEADPHONE CONNECTOR



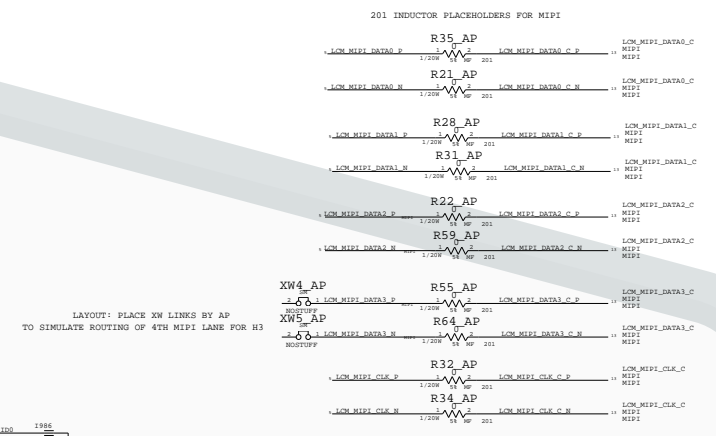
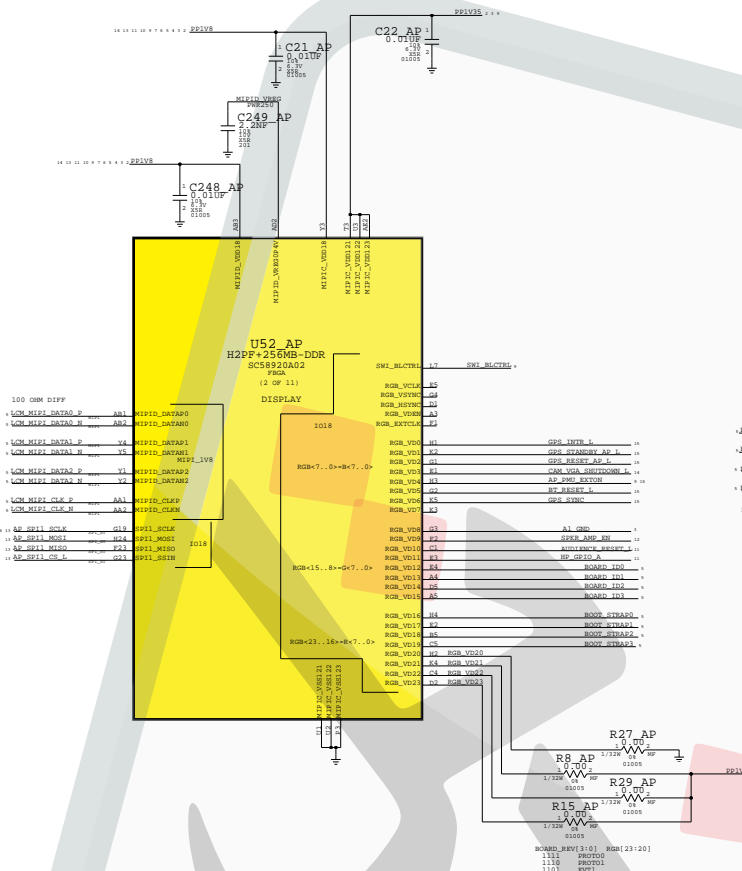
## BUTTON FLEX CONNECTOR



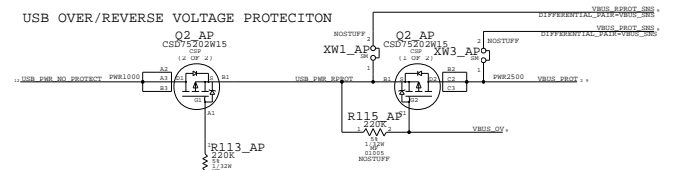
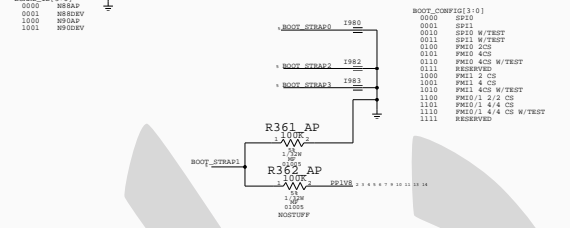


IPHONE

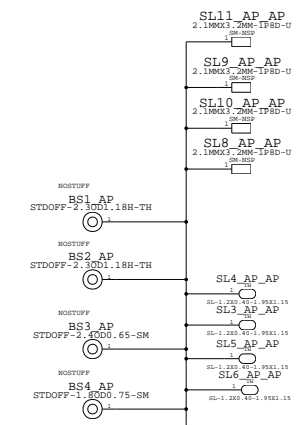
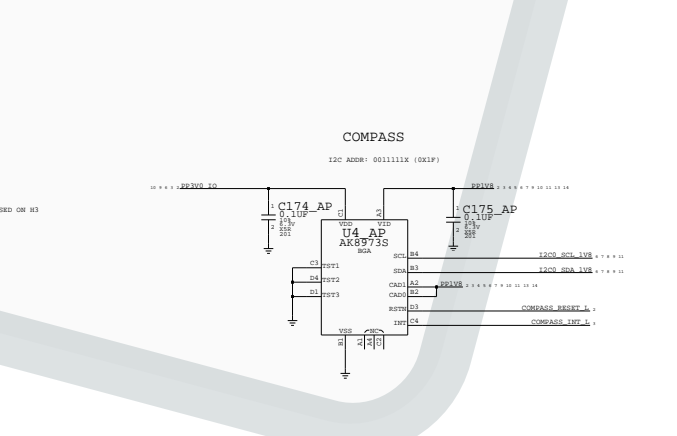
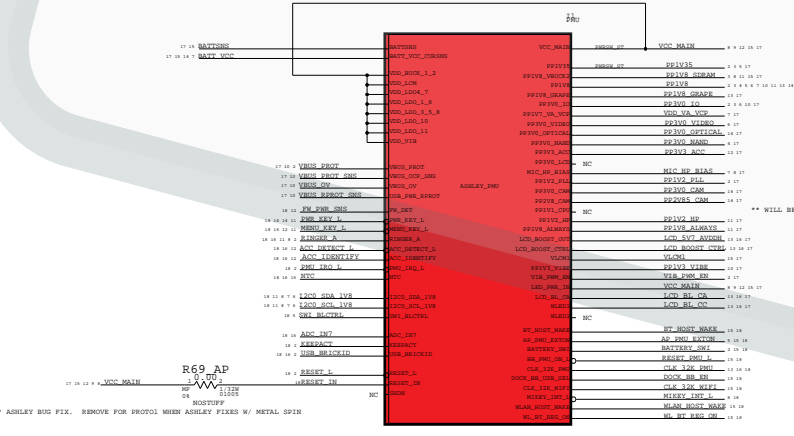
4



LAYOUT: PLACE XW LINES BY AP  
TO SIMULATE ROUTING OF 4TH MIPI LANE FOR H3



PP 17 - 18



\* ASHLEY BUG FIX. REMOVE FOR PROTEL WHEN ASHLEY FIXES W/ METAL SPIN



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4

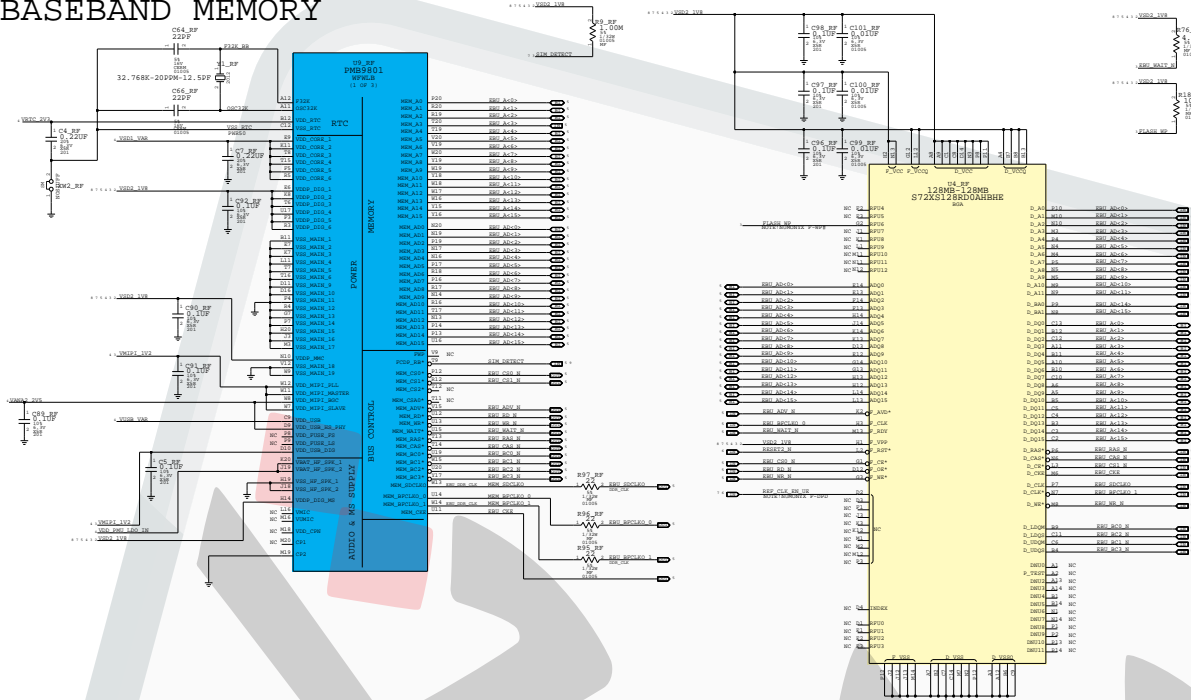


# شما تیک های مربوط به طبقه تلفن

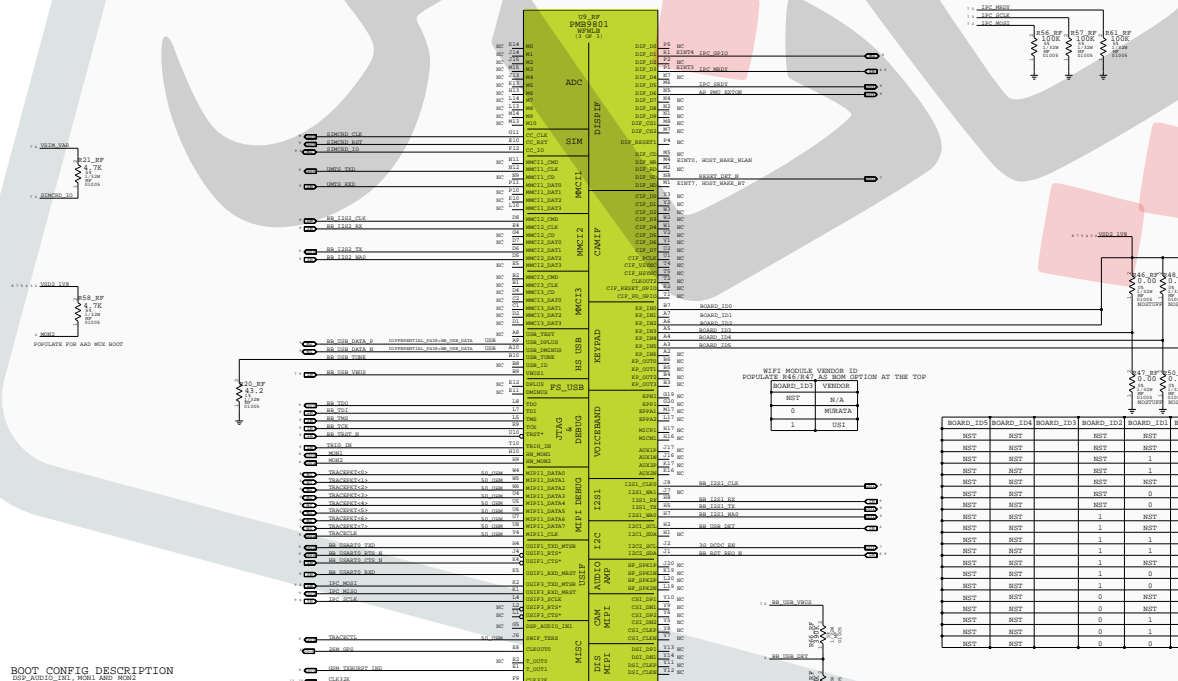




**BASEBAND MEMORY**



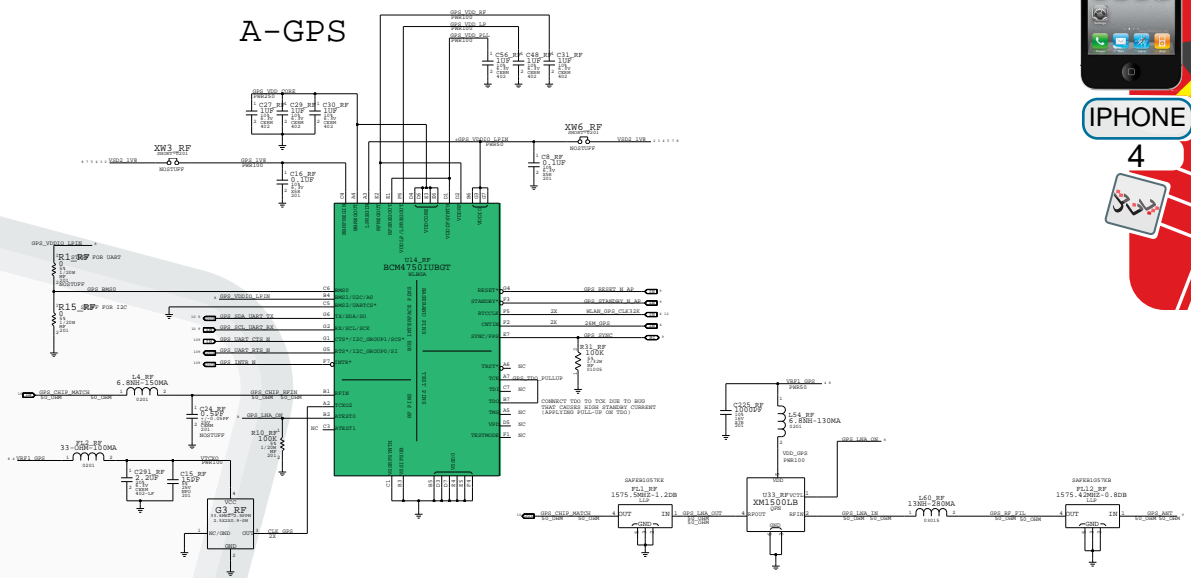
**BASEBAND AUDIO & IO**



**BOOT CONFIG DESCRIPTION**

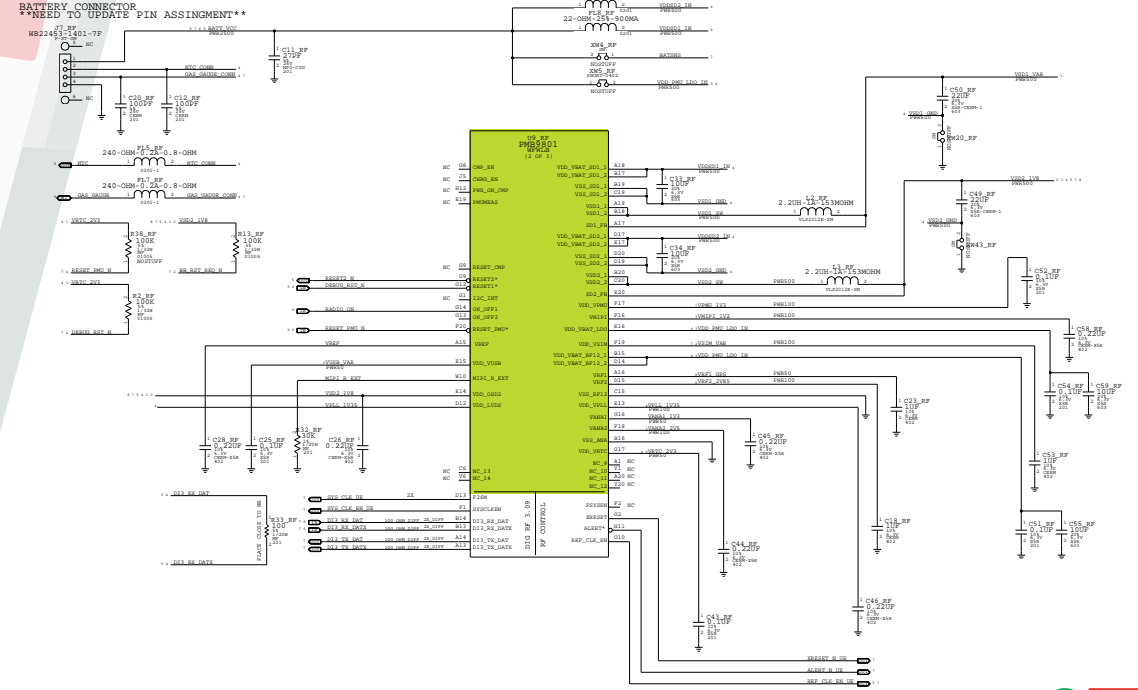
BOOT_CONFIG[1]	BOOT_CONFIG[2]	BOOT_CONFIG[3]	BOOT_CONFIG[4]	BOOT_CONFIG DESCRIPTION
0	0	0	0	EXTERNAL BOOT VIA USB
0	0	0	1	NON FLASH - 8MB COMPACT
0	0	1	0	NON FLASH - 16MB COMPACT
0	1	0	0	NON FLASH - 32MB COMPACT

**A-GPS**



I2C SLAVE ADDRESS 0X12/0X13

**BASEBAND POWER SUPPLY**

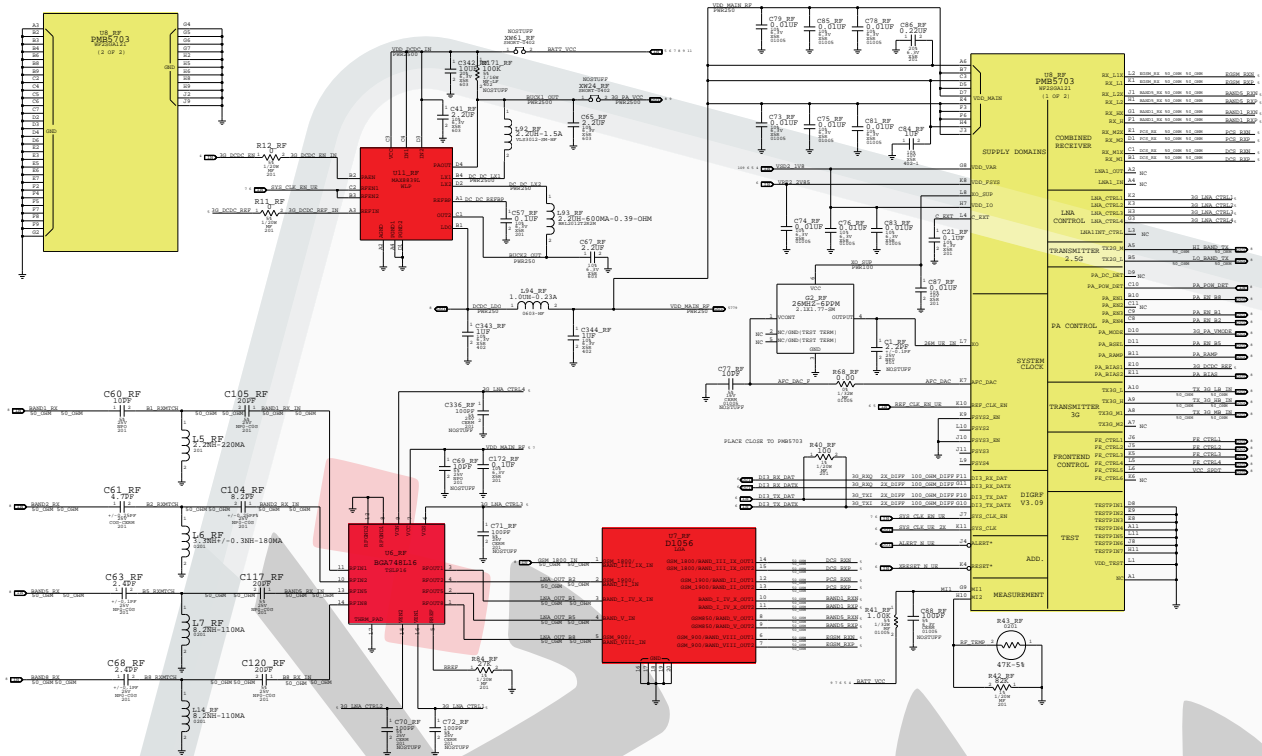


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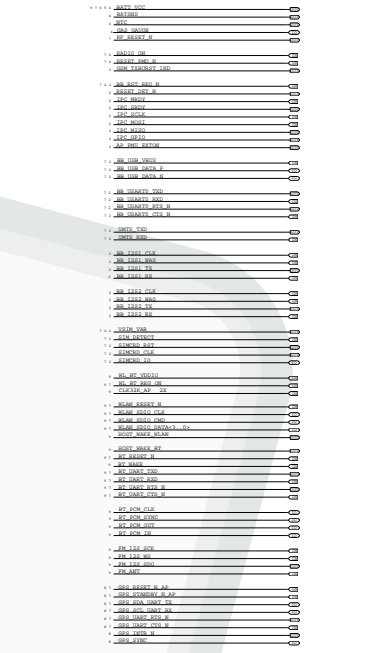
4



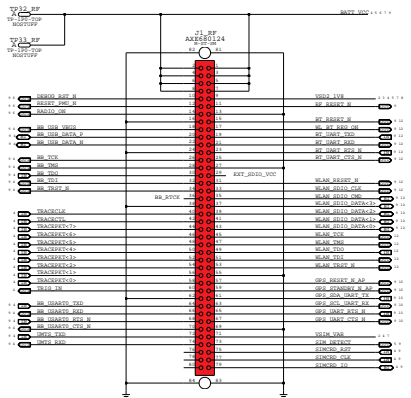
# GSM & UMTS TRANSCEIVER - SMART I UE



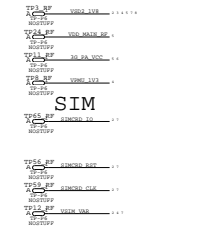
## SYSTEM CONNECTORS AP CONNECTIONS



## DEBUG CONNECTOR



## POWER DOMAINS



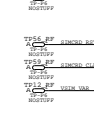
## USART0



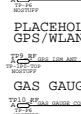
## CONTROL



## SIM



## FM



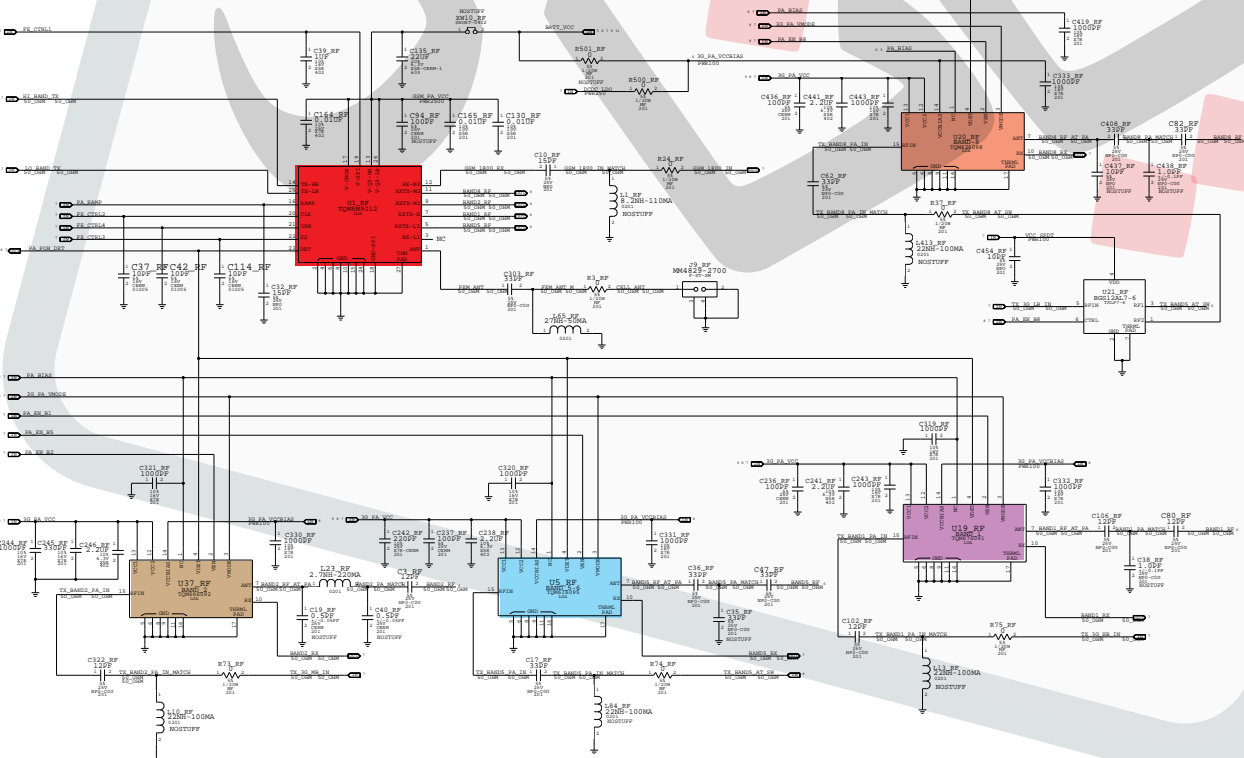
## JTAG



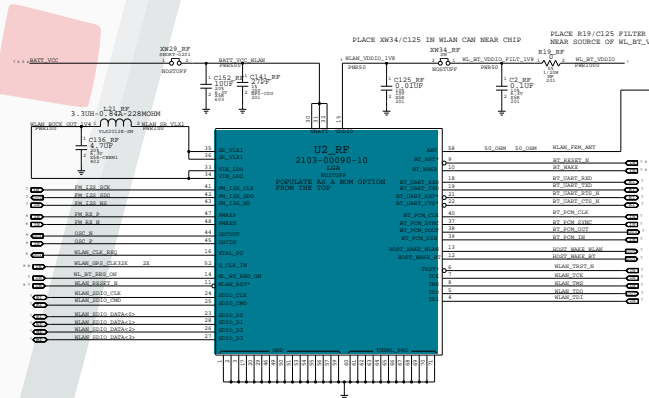
PLACEHOLDER FOR GPS/WLAN ANT PAD

GAS GAUGE

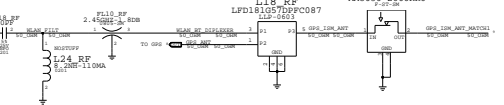
## POWER AMPS AND RF FRONT-END MODULE



## WLAN/BLUETOOTH/FM RADIO



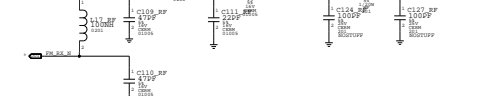
## RF FILTER, DIPLEXER, AND CONNECTOR



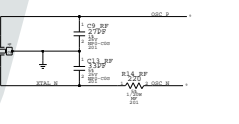
ANTENNA MATCH AND FEED  
CHANGE BY PROTOL!  
DO NOT NEED AN ANTENNA  
CONNECTOR



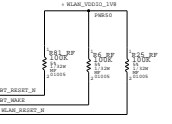
## FM INPUT



## REFERENCE OSCILLATOR CRYSTAL



## PULL UP RESISTORS



## PULL DOWN RESISTORS

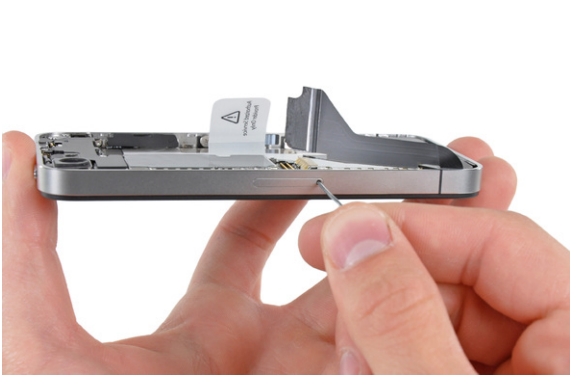
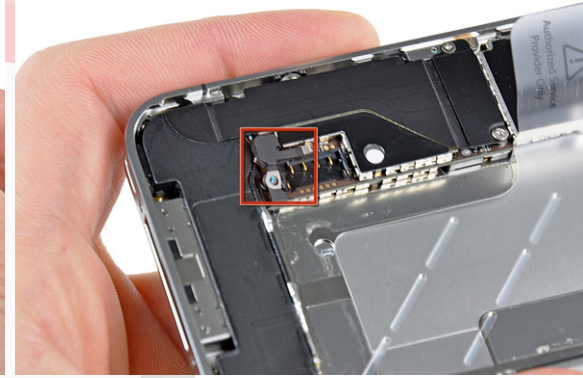


# تصاویر مربوط به باز کردن آیفون 4G

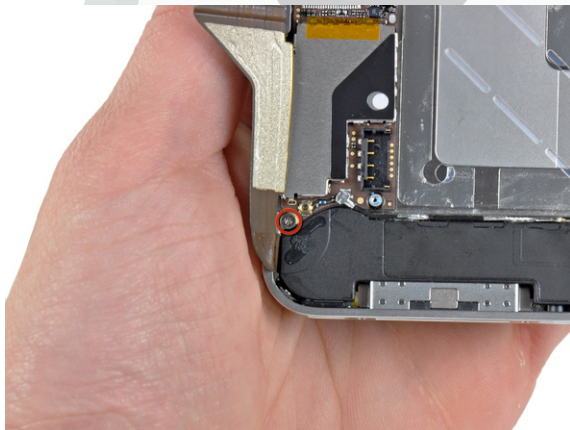


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## تصاویر مربوط به بازکردن آیفون 4G



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4

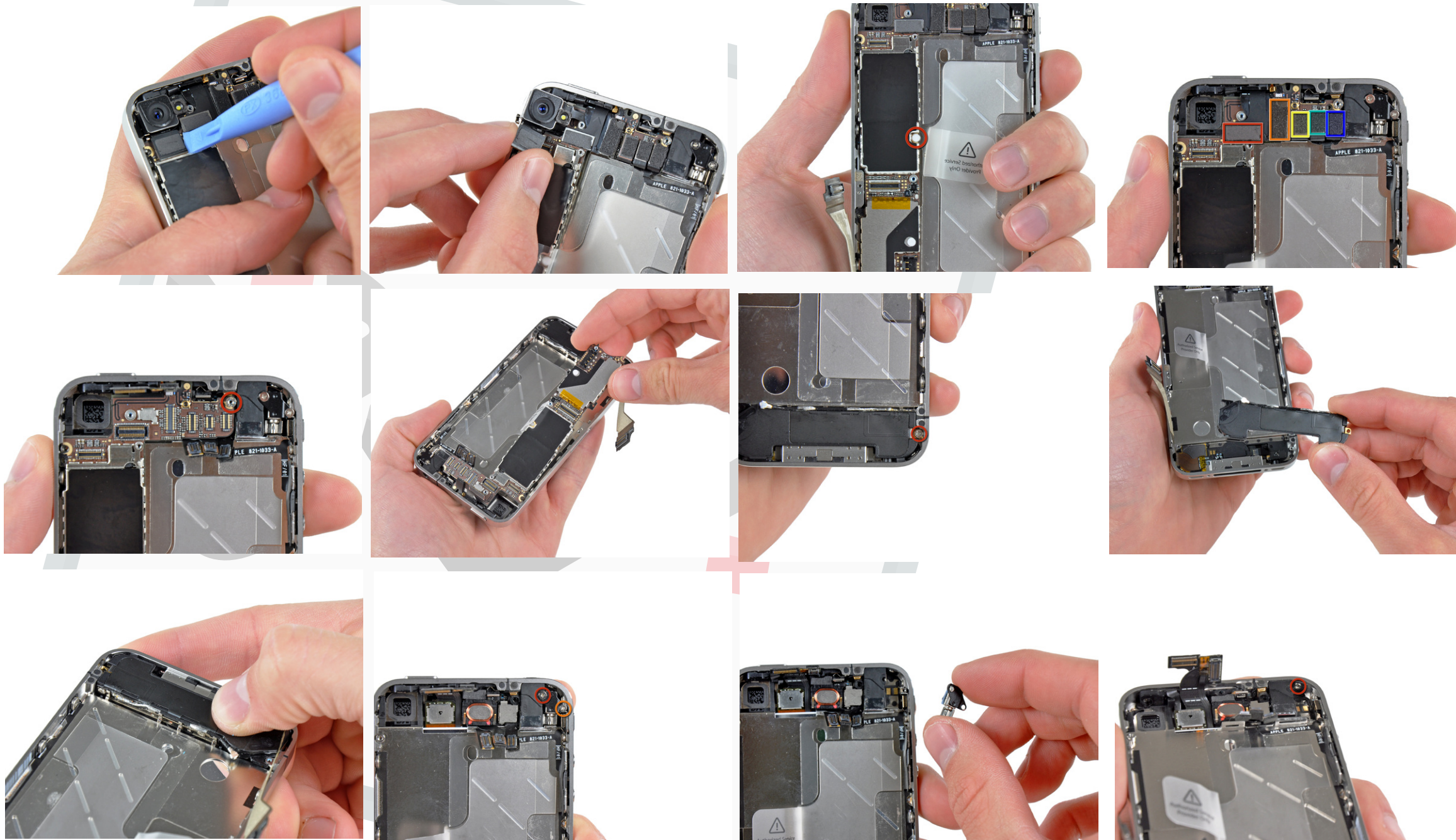


# تصاویر مربوط به بازکردن آیفون 4G



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4

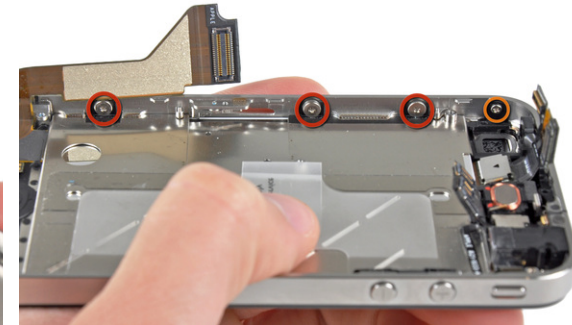


# تصاویر مربوط به باز کردن آیفون 4G



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4



# اطلاعات فنی مربوط به برخی از آی سی های بکار رفته در آیفون 4G



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4

## SN74LVC2G125-Q1

DUAL BUS BUFFER GATE WITH 3-STATE OUTPUTS

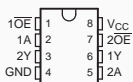


### FEATURES

- Qualified for Automotive Applications
- Supports 5-V  $V_{CC}$  Operation
- Inputs Accept Voltages to 5.5 V
- Max  $t_{pd}$  of 4.3 ns at 3.3 V
- Low Power Consumption, 10- $\mu$ A Max  $I_{CC}$
- $\pm 24$ -mA Output Drive at 3.3 V
- Typical  $V_{OLP}$  (Output Ground Bounce) <0.8 V at  $V_{CC} = 3.3$  V,  $T_A = 25^\circ\text{C}$
- Typical  $V_{OHV}$  (Output  $V_{OH}$  Undershoot) >2 V at  $V_{CC} = 3.3$  V,  $T_A = 25^\circ\text{C}$
- $I_{LH}$  Supports Partial-Power-Down Mode Operation
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II

- ESD Protection Exceeds JESD 22
  - 2000-V Human-Body Model (A114-A)
  - 200-V Machine Model (A115-A)
  - 1000-V Charged-Device Model (C101)

DCT OR DCU PACKAGE (TOP VIEW)



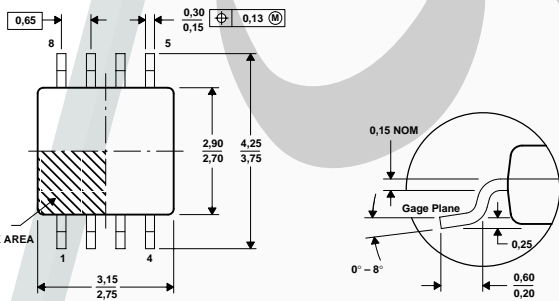
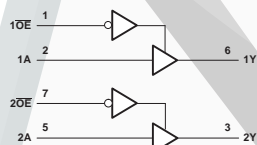
### DESCRIPTION/ORDERING INFORMATION

The SN74LVC2G125-Q1 is a dual bus buffer gate designed for 1.65-V to 5.5-V  $V_{CC}$  operation. This device features dual line drivers with 3-state outputs. The outputs are disabled when the associated output-enable (OE) input is high.

To ensure the high-impedance state during power up or power down, OE should be tied to  $V_{CC}$  through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

This device is fully specified for partial-power-down applications using  $I_{LH}$ . The  $I_{LH}$  circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

### LOGIC DIAGRAM (POSITIVE LOGIC)



## AK8973



3-axis Electronic Compass

### 1. Features

- 3-axis electronic compass IC
- Optimal built-in electronic compass for mobile phones and handy terminals
- High sensitivity Hall sensors are integrated.
- Functions
  - Built-in 8-bit ADC
  - Built-in amplifier for sensor signal amplification
  - Built-in 8-bit DAC for sensor signal offset compensation
  - Built-in EEPROM for storing individual adjustment values
  - Built-in temperature sensor
  - 8-bit digital output
  - Serial interface: I<sup>2</sup>C bus interface (supporting the low-voltage specification)
  - Automatic power-down function
  - Interrupt function for measurement data ready
  - Built-in master clock oscillator
- Operating temperatures: -30°C to +85°C
- Operating supply voltage: +2.5V to +3.6V
- Low current consumption/measurement time:
  - Power-down: 0.2 $\mu$ A typ.
  - Magnetic sensor driving: 6.8mA/12.6ms
- Package: 16-pin QFN package: 4.0mmx4.0mmx0.7mm

### 2. Overview

AK8973 is a geomagnetism detection type electronic compass IC.

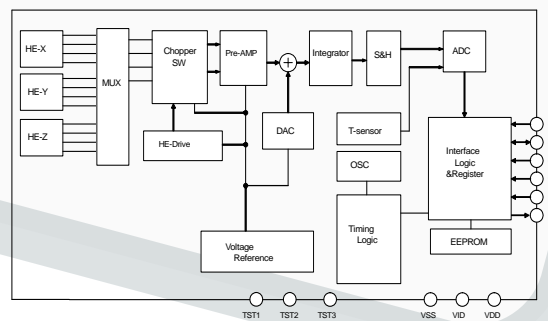
The small package of AK8973 integrates magnetic sensors for detecting geomagnetism in the X-axis, Y-axis, and Z-axis, and arithmetic circuit for processing the signal from each sensor. AK8973 outputs four data in total as 8-bit digital values respectively: 3-axis magnetic sensor measured values and temperature sensor read value. By processing the magnetic sensor measured values with an external CPU, azimuth data can be obtained.

By using AK8973 integrated into the system, a navigation system is achieved with reduced space in portable equipment such as PDA or mobile phone incorporating the GPS function.

Specifically, AK8973 has the following features:

- (1) Due to the built-in 8-bit ADC and serial interface, geomagnetism of the X-axis, Y-axis, and Z-axis can be detected as digital data.
- (2) The serial interface corresponds to the I<sup>2</sup>C bus.
- (3) A dedicated power supply is used for the serial interface, so the low-voltage specification can also be supported by applying 1.85V.
- (4) Due to the built-in DAC for compensating the offset magnetic field, the position restraint with parts which generate the offset magnetic field such as speakers is reduced, and the degree of freedom about layout is expanded. Note 1)
- (5) An EEPROM for storing the individual adjustment values of sensor sensitivity is built-in. The adjustment values are stored in factory at the time of shipment from AKM.
- (6) The built-in temperature sensor as an accessory generates the 8-bit digital A/D-converted value. The temperature information is not used for azimuth calculation.
- (7) The major circuit blocks of AK8973 are activated by the measurement request command from the controller, and transit to the power-down mode automatically at the end of measurement. That characteristic realizes the low power consumption required for mobile phones.
- (8) The interrupt function for posting the completion of sensor signal measurement to the external CPU is built-in.
- (9) The master clock oscillator is built-in. It is unnecessary to supply the clock from the outside.

### 3.1. Block Diagram



## AT25DF081

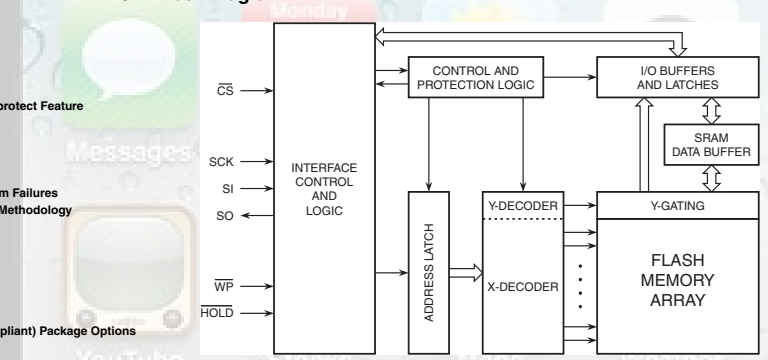
8-megabit  
1.65-volt  
Minimum  
SPI Serial Flash  
Memory



### Features

- Single 1.65V - 1.95V Supply
- Serial Peripheral Interface (SPI) Compatible
  - Supports SPI Modes 0 and 3
- 66 MHz Maximum Clock Frequency
- Flexible, Uniform Erase Architecture
  - 4-Kbyte Blocks
  - 32-Kbyte Blocks
  - 64-Kbyte Blocks
  - Full Chip Erase
- Individual Sector Protection with Global Protect/Unprotect Feature
  - Sixteen 64-Kbyte Physical Sectors
- Hardware Controlled Locking of Protected Sectors
- Flexible Programming
  - Byte/Page Program (1 to 256 Bytes)
- Automatic Checking and Reporting of Erase/Program Failures
- JEDEC Standard Manufacturer and Device ID Read Methodology
- Low Power Dissipation
  - 7 mA Active Read Current (Typical)
  - 8  $\mu$ A Deep Power-Down Current (Typical)
- Endurance: 100,000 Program/Erase Cycles
- Data Retention: 20 Years
- Complies with Full Industrial Temperature Range
- Industry Standard Green (Pb/Halide-free/RoHS Compliant) Package Options
  - 8-lead SOIC (150-mil wide)
  - 8-contact Ultra Thin DFN (5 mm x 6 mm x 0.6 mm)
  - 11-ball dBG (WLCSFP)

### 3. Block Diagram



### 1. Description

The AT25DF081 is a serial interface Flash memory device designed for use in a wide variety of high-volume consumer based applications in which program code is shadowed from Flash memory into embedded or external RAM for execution. The flexible erase architecture of the AT25DF081, with its erase granularity as small as 4-Kbytes, makes it ideal for data storage as well, eliminating the need for additional data storage EEPROM devices.

The physical sectoring and the erase block sizes of the AT25DF081 have been optimized to meet the needs of today's code and data storage applications. By optimizing the size of the physical sectors and erase blocks, the memory space can be used much more efficiently. Because certain code modules and data storage segments must reside by themselves in their own protected sectors, the wasted and unused memory space that occurs with large sector and large block erase Flash memory devices can be greatly reduced. This increased memory space efficiency allows additional code routines and data storage segments to be added while still maintaining the same overall device density.

Figure 2-1. 8-SOIC Top View

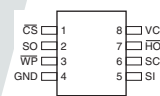


Figure 2-2. 8-UDFN Top View

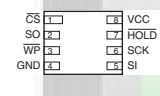
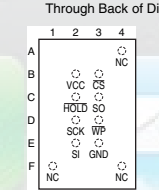


Figure 2-3. 11-dBG (Top View Through Back of Die)



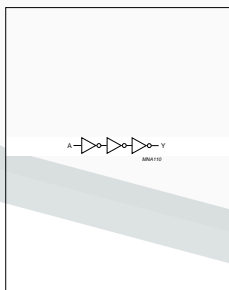
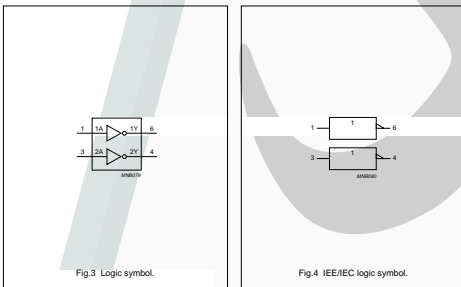
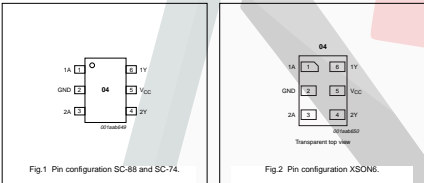
# اطلاعات فنی مربوط به برخی از آی سی های بکار رفته در آیفون 4G

## 74LVC2G04 Dual inverter



- FEATURES**
- Wide supply voltage range from 1.65 V to 5.5 V
  - 5 V tolerant input/output for interfacing with 5 V logic
  - High noise immunity
  - Complies with JEDEC standard:
    - JESD8-7 (1.65 V to 1.95 V)
    - JESD8-6 (2.3 V to 2.7 V)
    - JESD88/JESD88B (2.7 V to 3.6 V)
  - ESD protection:
    - HBM EIA/JESD22-A114-B exceeds 2000 V
    - MM EIA/JESD22-A115-A exceeds 200 V
  - 324 mA output drive ( $V_{CC} = 3.0 V$ )
  - CMOS low power consumption
  - Latch-up performance exceeds 250 mA
  - Direct interface with TTL levels
  - Multiple package options
  - Specified from -40 °C to +85 °C and -40 °C to +125 °C
- DESCRIPTION**
- The 74LVC2G04 is a high-performance, low-power, low-voltage, 50-gate CMOS device and superior to most advanced CMOS compatible TTL families. Inputs can be driven from either 3.3 V or 5 V devices. These features allow the use of these devices as translators in a mixed 3.3 V and 5 V environment. This device is fully specified for partial power-down applications using I<sub>DDQ</sub>. The I<sub>DDQ</sub> circuitry disables the output, preventing the damaging backflow current through the device when it is powered down. The 74LVC2G04 provides two inverting buffers.

PIN	SYMBOL	DESCRIPTION
1	1A	data input
2	GND	ground (0 V)
3	2A	data input
4	2Y	data output
5	V <sub>CC</sub>	supply voltage
6	1Y	data output



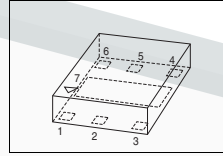
## BGS12AL7-6



SPDT RF Switch

### 1 Features

- Main features:**
- Low insertion loss
  - High port-to-port-isolation
  - Low harmonic generation
  - On-chip control logic, only one control line required
  - High ESD robustness
  - No external components required
  - General purpose switch for applications up to 3 GHz
  - Small leadless package TSLP-7-6
  - Lead and halogen free package (RoHS and WEEE compliant)



### Description

The BGS12AL7-6 General Purpose RF MOS switch is designed to cover a broad range of applications from 30 MHz to 3 GHz. The symmetric design of its single pole double throw configuration, as shown in Figure 1 offers high design flexibility. This single supply chip integrates on-chip CMOS logic driven by a simple, single-pin CMOS or TTL compatible control input signal. The 0.1 dB compression point exceeds the switch's maximum input power level of 21 dBm, resulting in linear performance at all signal levels. The RF switch has a very low insertion loss of 0.4 dB in the 1 GHz and 0.5 dB in the 2 GHz range.

Unlike GaAs technology, external DC blocking capacitors at the RF ports are only required if DC voltage is applied externally.

The BGS12AL7-6 RF switch is manufactured in Infineon's patented MOS technology, offering the performance of GaAs with the economy and integration of conventional CMOS including the inherent higher ESD robustness.

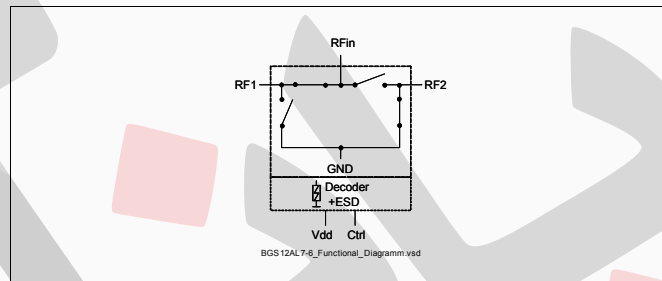


Figure 1 Functional Diagram

### Pin Description

Table 3 Pin Description

Pin No.	Name	Pin Type	Buffer Type	Function
1	RF2	I/O		RF Port 2 Out
2	GND	GND		Ground
3	RF1	I/O		RF Port 1 Out
4	Vdd	PWR		Supply Voltage
5	RFIN	I/O		RF Port In
6	CTRL	I		Control Pin
7	NC	NC		It is recommended to connect Pin 7 to Ground

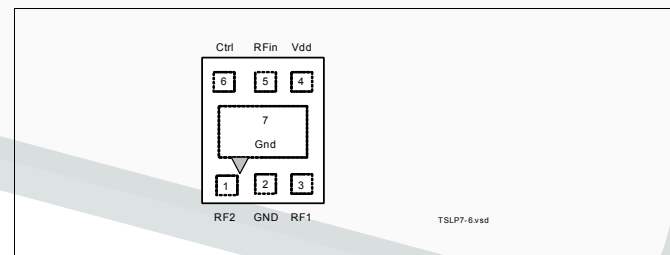


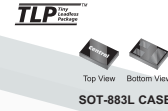
Figure 2 Pin Configuration (top view)

Table 4 Truth Table

Ctrl 1	RF 1	RF 2
0	1	0
1	0	1

## CEDM7001

SURFACE MOUNT  
N-CHANNEL  
ENHANCEMENT-MODE  
SILICON MOSFET



### DESCRIPTION:

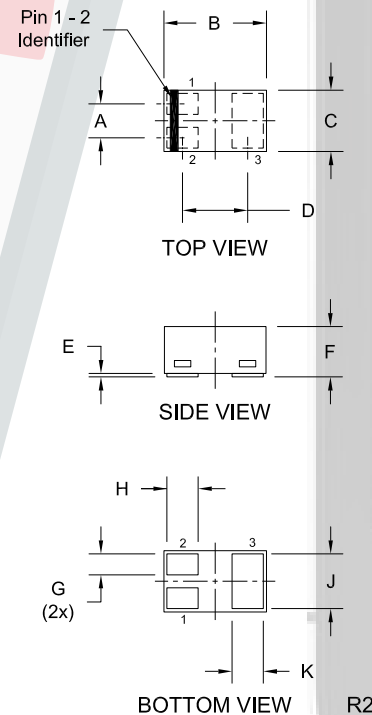
The CENTRAL SEMICONDUCTOR CEDM7001 is an N-Channel Enhancement-mode Field Effect Transistor, manufactured by the N-Channel DMOS Process, designed for high speed pulsed amplifier and driver applications. This MOSFET offers Low  $r_{DS(on)}$  and Low Threshold Voltage.

### FEATURES:

- 100mW Power Dissipation
- 0.4mm Low Package Profile
- Low  $r_{DS(on)}$
- Low Threshold Voltage
- Logic Level Compatible
- Small, TLP™ 1x0.6mm, SOT-883L Leadless Surface Mount Package

### APPLICATIONS:

- Load/Power Switches
- DC/DC Converters
- Battery Powered Portable Equipment



## FDFME3N311ZT



FDFME3N311ZT  
Integrated N-Channel PowerTrench® MOSFET and Schottky Diode  
30 V, 1.6 A, 299 mΩ

### Features

- Max  $r_{DS(on)}$  = 299 mΩ at  $V_{GS} = 4.5 V, I_D = 1.6 A$
- Max  $r_{DS(on)}$  = 410 mΩ at  $V_{GS} = 2.5 V, I_D = 1.3 A$
- Low profile: 0.55 mm maximum in the new package MicroFET 1.6x1.6 Thin
- Free from halogenated compounds and antimony oxides
- HBM ESD protection level > 1600V (Note3)
- RoHS Compliant

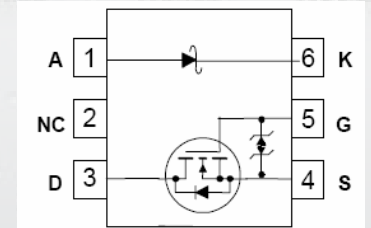
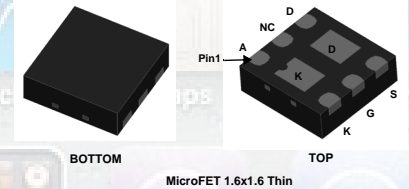
### General Description

This device is designed specifically as a single package solution for a boost topology in cellular handset and other ultra-portable applications. It features a MOSFET with low input capacitance, total gate charge and on-state resistance. An independently connected schottky diode with low forward voltage and reverse leakage current to maximize boost efficiency.

The MicroFET 1.6x1.6 Thin package offers exceptional thermal performance for its physical size and is well suited to switching and linear mode applications.

### Applications

- Boost Functions



4